



# 2A, 200V - 1000V High Efficient Surface Mount Rectifier

#### **FEATURES**

- Glass passivated chip junction
- Ideal for automated placement
- Low reverse leakage
- Moisture sensitivity level: level 1, per J-STD-020
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

#### **APPLICATIONS**

- DC to DC converter
- Switching mode converters and inverters
- Freewheeling application

#### **MECHANICAL DATA**

· Case: SMAF

• Molding compound meets UL 94V-0 flammability rating

• Terminal: Matte tin plated leads, solderable per J-STD-002

Meet JESD 201 class 1 whisker test

• Polarity: Indicated by cathode band

• Weight: 0.035g (approximately)

KEY PARAMETERS			
PARAMETER	VALUE	TINU	
I <sub>F</sub>	2	Α	
$V_{RRM}$	200 - 1000	V	
I <sub>FSM</sub>	50	Α	
T <sub>J MAX</sub>	150	°C	
Package	SMAF		
Configuration	Single die		









**SMAF** 



PARAMETER		SYMBOL	HS2D	HS2G	HS2J	HS2K	HS2M	UNIT
			AF-T	AF-T	AF-T	AF-T	AF-T	
Marking code on the de	vice		HS2DAF	HS2GAF	HS2JAF	HS2KAF	HS2MAF	
Repetitive peak reverse	voltage	$V_{RRM}$	200	400	600	800	1000	V
Reverse voltage, total rms value		V <sub>R(RMS)</sub>	140	280	420	560	700	V
Forward current I <sub>F</sub> 2		2			Α			
Surge peak forward current single half sine-		1	50				Α	
wave superimposed on rated load	t = 1.0ms	I <sub>FSM</sub>			130			Α
Junction temperature		$T_J$	-55 to +150		°C			
Storage temperature		T <sub>STG</sub>	-55 to +150		°C			

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THERMAL PERFORMANCE				
PARAMETER	SYMBOL	TYP	UNIT	
Junction-to-lead thermal resistance	R <sub>OJL</sub>	15	°C/W	
Junction-to-ambient thermal resistance	R <sub>eJA</sub>	89	°C/W	
Junction-to-case thermal resistance	R <sub>eJC</sub>	22	°C/W	

**Thermal Performance Note:** Units mounted on PCB (5mm x 5mm Cu pad test board)

PARAMETER		CONDITIONS	SYMBOL	TYP	MAX	UNIT
	HS2DAF-T	I <sub>F</sub> = 1A, T <sub>J</sub> = 25°C		0.84	-	V
		I <sub>F</sub> = 2A, T <sub>J</sub> = 25°C		0.91	1.00	V
		I <sub>F</sub> = 1A, T <sub>J</sub> = 125°C		0.68	-	V
		I <sub>F</sub> = 2A, T <sub>J</sub> = 125°C		0.78	0.94	V
		I <sub>F</sub> = 1A, T <sub>J</sub> = 25°C		0.94	-	V
<b>5</b>	LICOCAET	I <sub>F</sub> = 2A, T <sub>J</sub> = 25°C	.,	1.04	1.40	V
Forward voltage <sup>(1)</sup>	HS2GAF-T	I <sub>F</sub> = 1A, T <sub>J</sub> = 125°C	V <sub>F</sub>	0.77	-	V
		I <sub>F</sub> = 2A, T <sub>J</sub> = 125°C		0.88	1.07	V
		I <sub>F</sub> = 1A, T <sub>J</sub> = 25°C		1.19	-	V
	HS2JAF-T	I <sub>F</sub> = 2A, T <sub>J</sub> = 25°C		1.33	1.70	V
	HS2KAF-T HS2MAF-T	I <sub>F</sub> = 1A, T <sub>J</sub> = 125°C		0.96	-	V
		I <sub>F</sub> = 2A, T <sub>J</sub> = 125°C		1.10	1.31	V
Reverse current @ rated V <sub>R</sub> <sup>(2)</sup>		T <sub>J</sub> = 25°C	- I <sub>R</sub>	-	5	μΑ
		T <sub>J</sub> = 125°C		-	250	μΑ
	HS2DAF-T HS2GAF-T	I <sub>F</sub> = 0.5A, I <sub>B</sub> = 1.0A	t <sub>rr</sub>	-	50	ns
Reverse recovery time	HS2JAF-T HS2KAF-T HS2MAF-T	I <sub>rr</sub> = 0.25A		-	75	ns
Junction capacitance	HS2DAF-T		CJ	27	-	pF
	HS2GAF-T	4841 1/ 401/		21	-	pF
	HS2JAF-T HS2KAF-T HS2MAF-T	1MHz, $V_R = 4.0V$		12	-	pF

#### Notes:

- 1. Pulse test with PW = 0.3ms
- 2. Pulse test with PW = 30ms

ORDERING INFORMATION			
ORDERING CODE <sup>(1)</sup>	PACKAGE	PACKING	
HS2xAF-T	SMAF	7,500 / Tape & Reel	

#### Notes:

1. "x" defines voltage from 200V (HS2DAF-T) to 1000V (HS2MAF-T)



#### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

**Fig.1 Forward Current Derating Curve** 

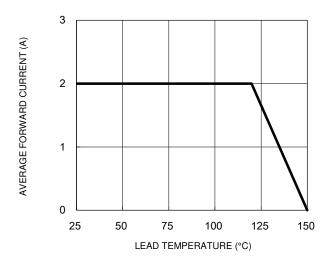


Fig.3 Typical Reverse Characteristics

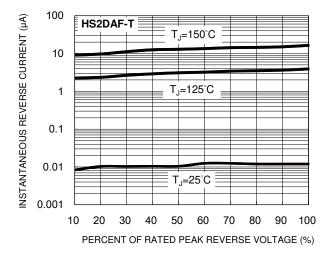


Fig.5 Typical Reverse Characteristics

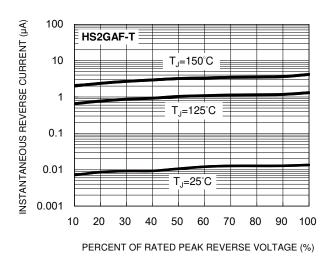


Fig.2 Typical Junction Capacitance

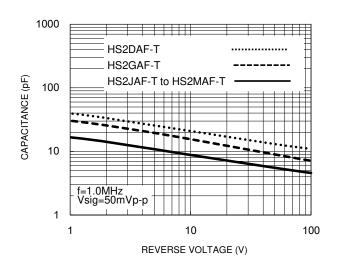


Fig.4 Typical Forward Characteristics

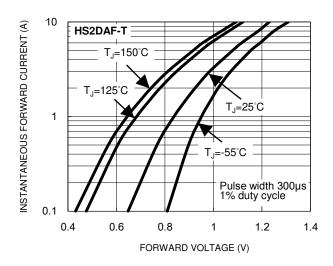
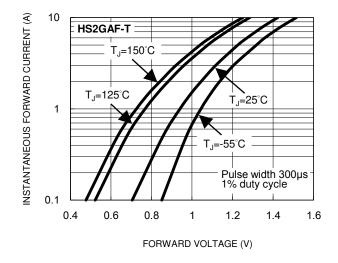


Fig.6 Typical Forward Characteristics





#### **CHARACTERISTICS CURVES**

(T<sub>A</sub> = 25°C unless otherwise noted)

Fig.7 Typical Reverse Characteristics

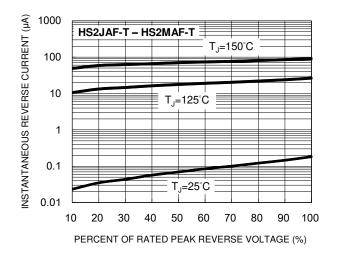


Fig.8 Typical Forward Characteristics

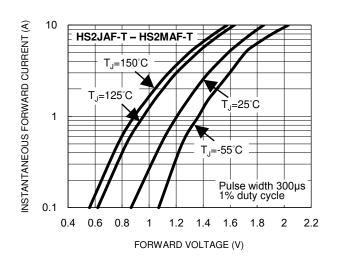
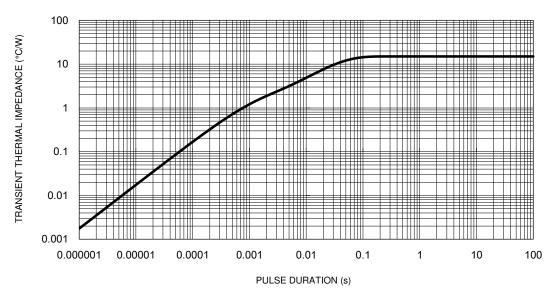


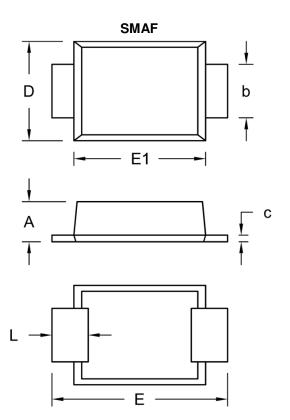
Fig.9 Typical Transient Thermal Impedance





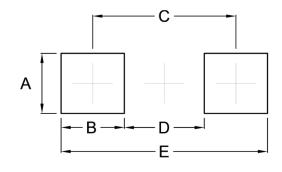
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#### **PACKAGE OUTLINE DIMENSIONS**



DIM. Unit (n		(mm)	m) Unit (inch)		
Dilvi.	Min.	Max.	Min.	Max.	
Α	1.00	1.10	0.039	0.043	
b	1.30	1.50	0.051	0.059	
С	0.10	0.25	0.004	0.010	
D	2.40	2.80	0.094	0.110	
E	4.40	4.80	0.173	0.189	
E1	3.25	3.65	0.128	0.144	
L	0.70	1.20	0.028	0.047	

## **SUGGESTED PAD LAYOUT**



Symbol	Unit (mm)	Unit (inch)
Α	1.57	0.062
В	1.66	0.065
С	3.76	0.148
D	2.10	0.083
E	5.42	0.213

# **MARKING DIAGRAM**



P/N = Marking Code

G = Green Compound

YW = Date Code

F = Factory Code



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